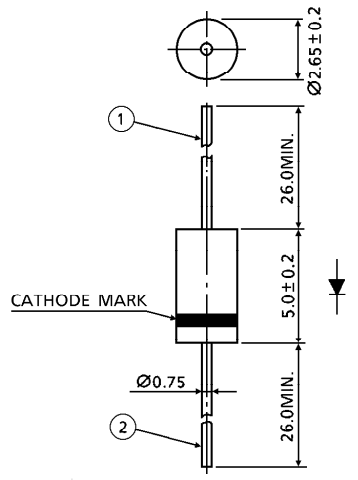
TOSHIBA RECTIFIER SILICON DIFFUSED TYPE

0R8GU41

HIGH SPEED RECTIFIER APPLICATIONS
(FAST RECOVERY)

- Average Forward Current : $I_{F(AV)}$ = 0.8A (Ta = 40°C)
- Repetitive Peak Reverse Voltage : V_{RRM} = 200~400V
- Reverse Recovery Time : t_{rr} = 100ns (Max.)
- Plastic Mold Type.

Unit in mm



1. ANODE
2. CATHODE

JEDEC	DO-41
EIAJ	—
TOSHIBA	3-3C1A

Weight : 0.3g

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	400	V
Average Forward Current (Ta = 40°C)	$I_{F(AV)}$	0.8	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	30 (50Hz)	A
		33 (60Hz)	
Junction Temperature	T_j	−40~150	°C
Storage Temperature Range	T_{stg}	−40~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	I_{FM} = 1.0A	—	1.5	V
Repetitive Peak Reverse Current	I_{RRM}	V_{RRM} = 400V	—	50	μA
Reverse Recovery Time	t_{rr}	I_F = 1.0A, di / dt = −30A / μs	—	100	ns
Forward Recovery Time	t_{fr}	I_F = 1.0A	—	200	ns
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	—	115	°C / W
Thermal Resistance	$R_{th(j-\ell)}$	Junction to Lead	—	45	°C / W

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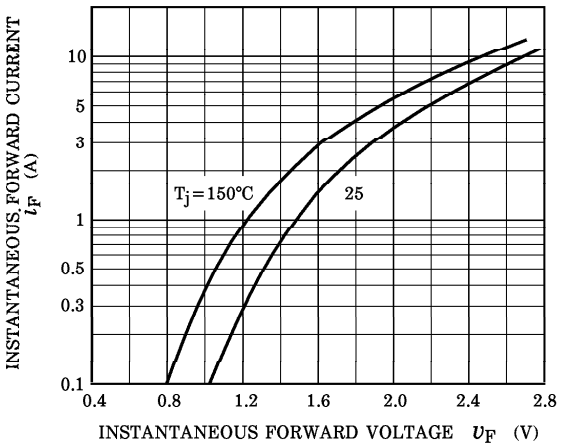
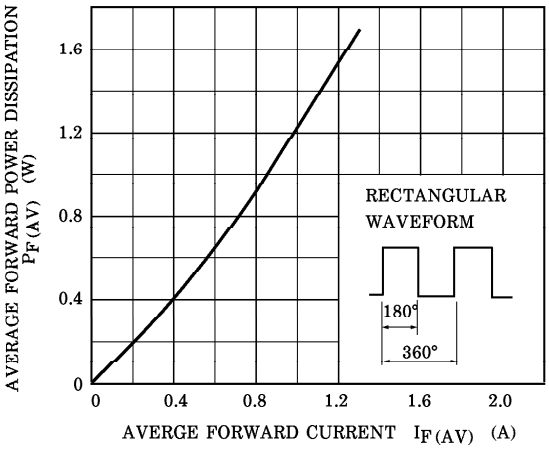
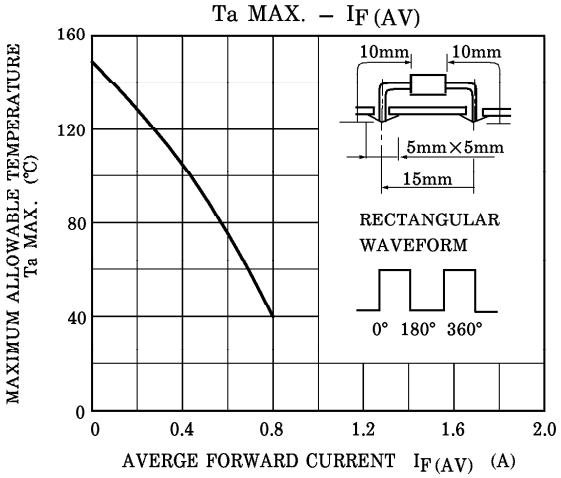
$i_F - v_F$



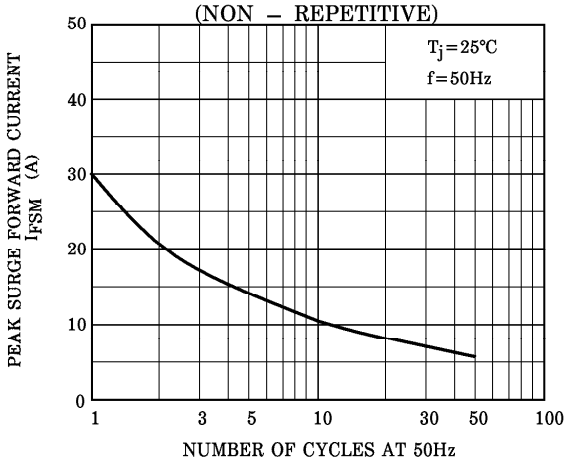
$P_{F(AV)} - I_{F(AV)}$



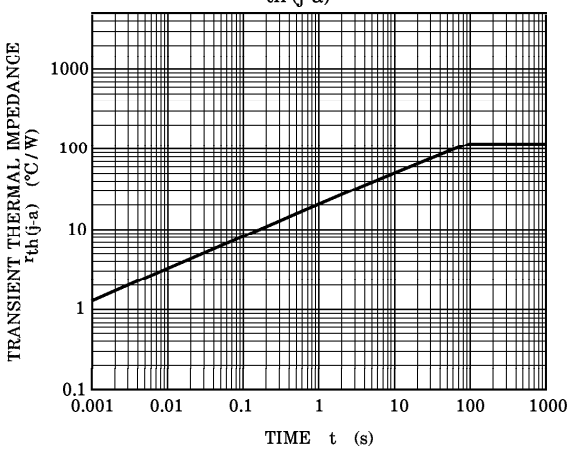
Ta MAX. – $I_{F(AV)}$



SURGE FORWARD CURRENT (NON – REPETITIVE)



$r_{th(j-a)} - t$



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